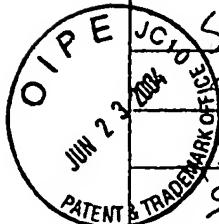


Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION <small>(Use several sheets if necessary)</small>	Doctor Number (Optional) NUS-03-001	Application Number 10/802,563
	<small>Applicant</small> <u>Hong Yn Yn et al.</u>	
	<small>Filing Date</small> <u>03/17/04</u>	<small>Group Art Unit</small>

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
JK	622516815/10/01		Gardner et al.	438	287	6/4/98
JK	63838795/7/02		Kizilayali et al.	438	303	5/17/00
JK	6511911/1/28/03		Besser et al.	438	656	4/3/01
SK	66176249/9/03		Powell	257	288	3/15/01
SK	60431573/28/00		Gardner et al.	438	692	12/18/97
SK	591602709/28/99		Misra et al.	438	197	8/11/97
SK	60838367/4/00		Rodder	438	690	12/18/98
SK	65769676/10/03		Schaeffer, III et al.	257	411	9/18/00
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SK	60514874/18/00		Gardner et al.	438	585	12/18/97



FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (*Including Author, Title, Date, Portion or Pages, Etc.*)

SK	-	Heuss et al., Abstract C7.6 "Thermal Stability of Hafnium and Hafnium Nitride (HfN_x) Gate Electrodes on Silicon Dioxide," pp. 67, 76-77, Materials Res. Soc. Proc., April 2000.
SK	-	"Physical and Electrical Properties of Metal Gate Electrodes on HfO_2 Gate Dielectrics" by J.K. Schaeffer et al., Journal of Vacuum Science and Tech., Vol. 21(1), Jan/Feb. 2003, pp. 11-17.
SK		
EXAMINER		DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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Doctor Number (Optional)

Application Number

NUS - 03 - 001

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Hong Yu Yu et al.

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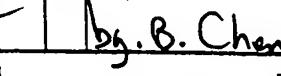
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U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (*Including Author, Title, Date, Portion or Pages, Etc.*)

SK	"Thermal Stability of PVD TiN Gate and Its Impacts on Characteristics of CMOS Transistors," by M. Wang et al., 6th Int'l Symp. on Plasma Process Induced Damage, May 14-15, 2001, Monterey, CA, USA, pp. 36-39.
SK	"Metal Gates for Advanced Sub-80-nm SOI CMOS Technology," by B. Cheng et al., 2001 IEEE Int'l SOI Conf., 10/01, pp. 91-92.
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	Applicant Heng Yu Yu et al.	
	Filing Date 03/17/04	Group Art Unit

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SK - "Properties and Microelectronic Applications of Thin Films of Refractory Metal Nitrides," by M.Wittner, Jr.,
of Vacuum Science Tech. A, Vol. 3, pp. 1797-1803.

SK - "Int'l Tech. Roadmap for Semiconductor," Semiconductor Industry Association, San Jose, CA
(ITRS-2003).

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al. 9605

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	Applicant Hong Yu Yu et al.	
	Filing Date 03/17/04	Group Art Unit

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FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

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SK	-	US Patent App. Pub. US 2003/0197230 A1 to Macuta et al., Pub. Date 10/23/03, Filed 04/19/02, US Class 257(407)
	-	US Patent App. Pub. US 2002/0037615 A1 to Matsuo, Pub. Date 03/28/02, Filed 09/25/01, US Class 438(241).

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